VUTJ010R11ANA

Datasheet

General Description

$V_{(BR)DSS}$	$R_{DS(ON)\_max}$	I_D
100V	105mΩ@10V	15A

Symbol

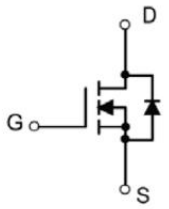
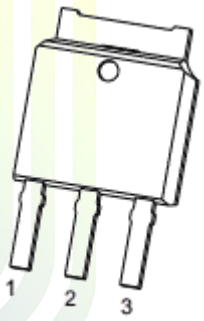


Figure 1 Symbol of VUTJ010R11ANA

Features

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Package Type



TO-251-3L

Figure 2 Package Type of VUTJ010R11ANA

Application

- Power switching application

Ordering Information

Product Name	Package
VUTJ010R11ANA	TO-251-3L

Absolute Maximum Ratings (T_A= 25 ºC, unless otherwise specified)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current[Note1]	T_C= 25 ºC	I_D	15	A
Pulsed Drain Current [Note2]		I_{DM}	45	
Single Pulse Avalanche Energy[Note3]		E_{AS}	12	mJ
Total Power Dissipation[Note5]	T_C= 25 ºC	P_D	1.25	W
Junction Temperature		T_J	150	ºC
Storage Temperature		T_{STG}	-55 to 150	ºC

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Ambient [Note6]	$R_{\theta JA}$		100		ºC/W

Electrical Characteristics (T_J= 25 ºC, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D= 250uA	100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}= 80V, V_{GS}=0V			1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS}= 0V			±100	nA
Gate Threshold Voltage[Note4]	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1.0	2.0	3.0	V
Static Drain-Source On-Resistance[Note4]	$R_{DS(ON)}$	V_{GS}=10V, I_D= 8A		76	105	mΩ
Dynamic Characteristics						
Input Capacitance	C_{ISS}	V_{DS}=30V		580		pF
Output Capacitance	C_{OSS}	V_{GS}=0V		50		pF
Reverse Transfer Capacitance	C_{RSS}	f=1MHz		40		pF
Total Gate Charge	Q_g	V_{DS}=30V		17		nC
Gate-Source Charge	Q_{gs}	V_{GS}=10V		4		
Gate-Drain Charge	Q_{gd}	I_D=3A		5		
Switching Parameters						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}= 30V		13		ns
Turn-on Rise Time	t_r	V_{GS}= 10V		8		
Turn-off Delay Time	$t_{d(off)}$	R_L=15Ω		25		
Turn-off Fall Time	t_f	R_G=2.5Ω		11		
Diode Characteristics						
Diode Forward Voltage [Note4]	V_{SD}	V_{GS}=0V, I_S= 10A		0.85	1.2	V

Notes :

1.The maximum current rating is limited by package.And device mounted on a large heatsink

2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.

3.E_{AS} condition: V_{DD} = 15V,V_{GS} = 10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.

4.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

5.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.And device mounted on a large heatsink

6.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

Typical Performance Characteristics

Figure 3: Transfer Characteristics

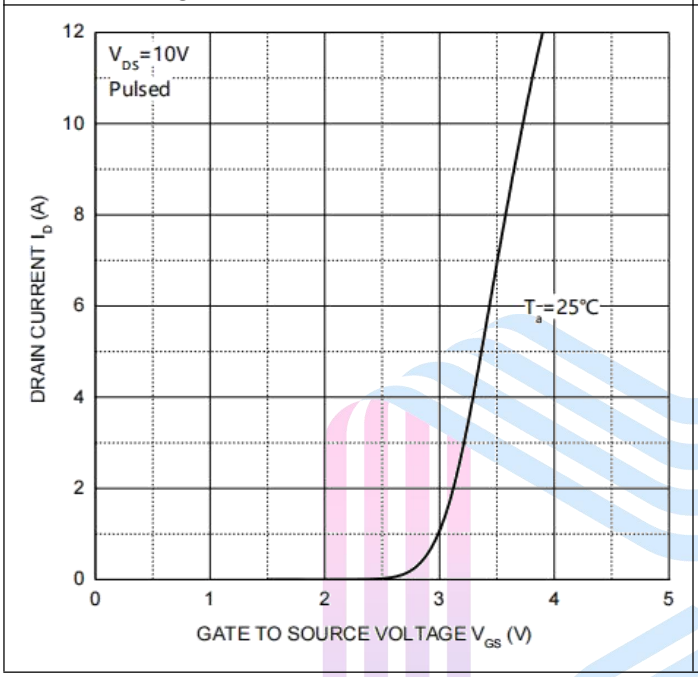


Figure 4: Output Characteristics

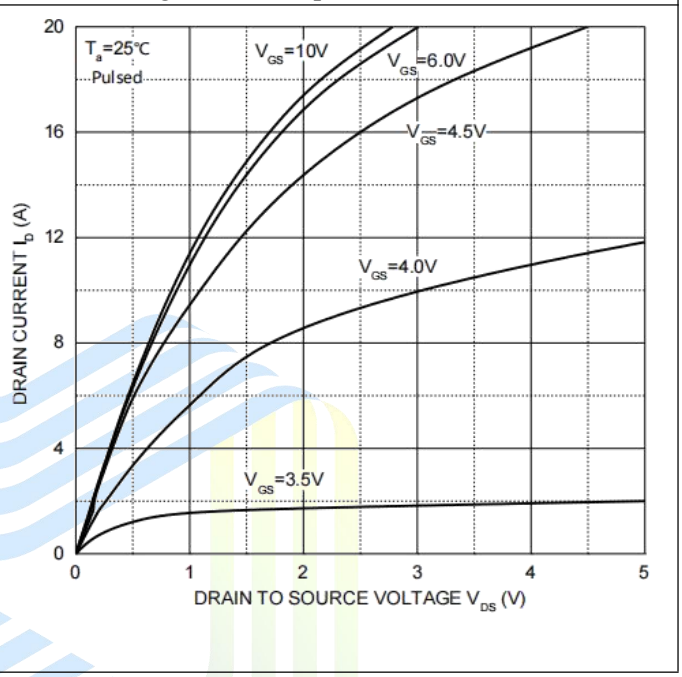


Figure 5: On-Resistance vs. Drain Current

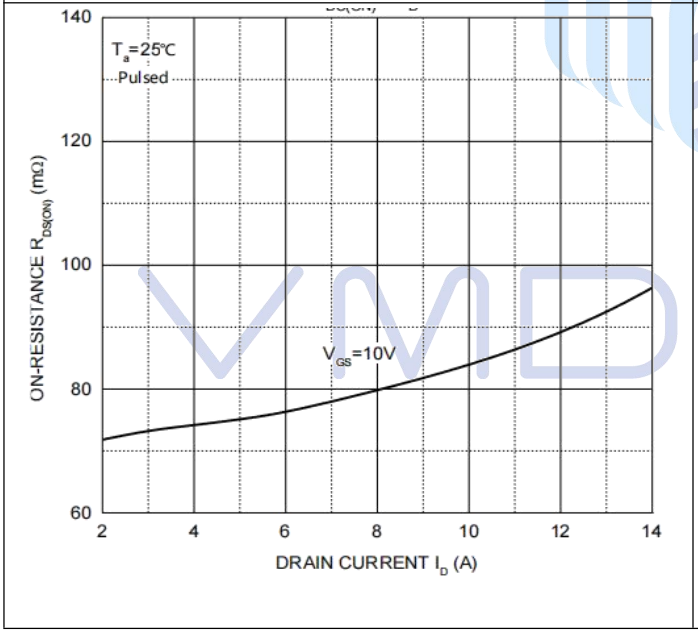


Figure 6: On-Resistance vs. Gate Voltage

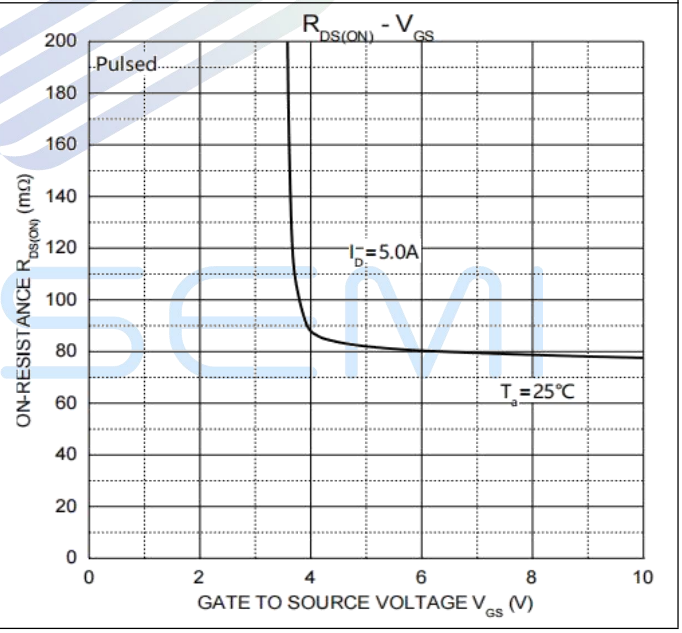


Figure 7: Body Diode Characteristics

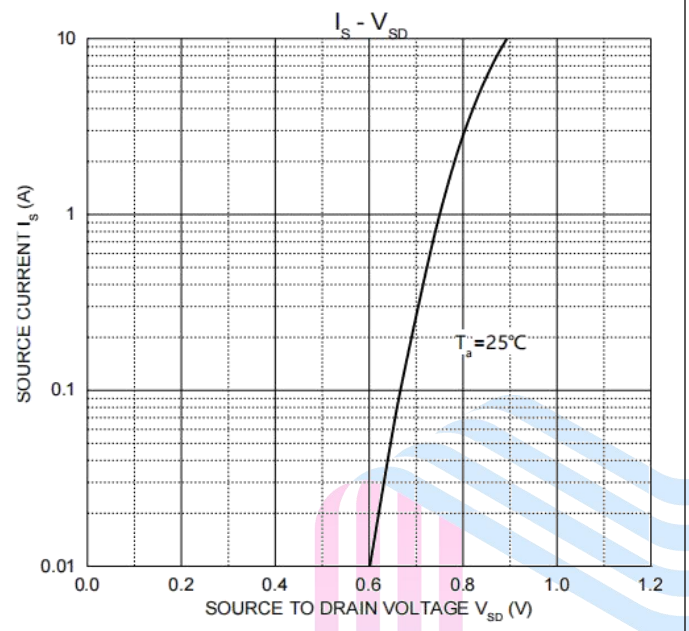
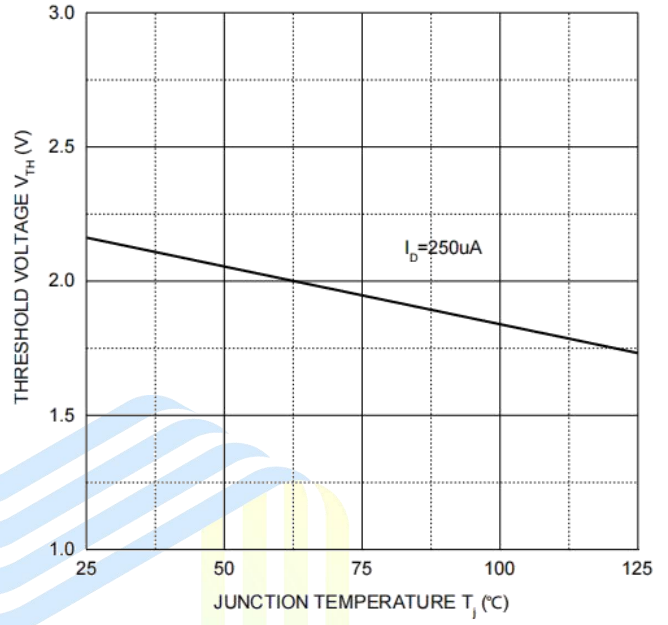
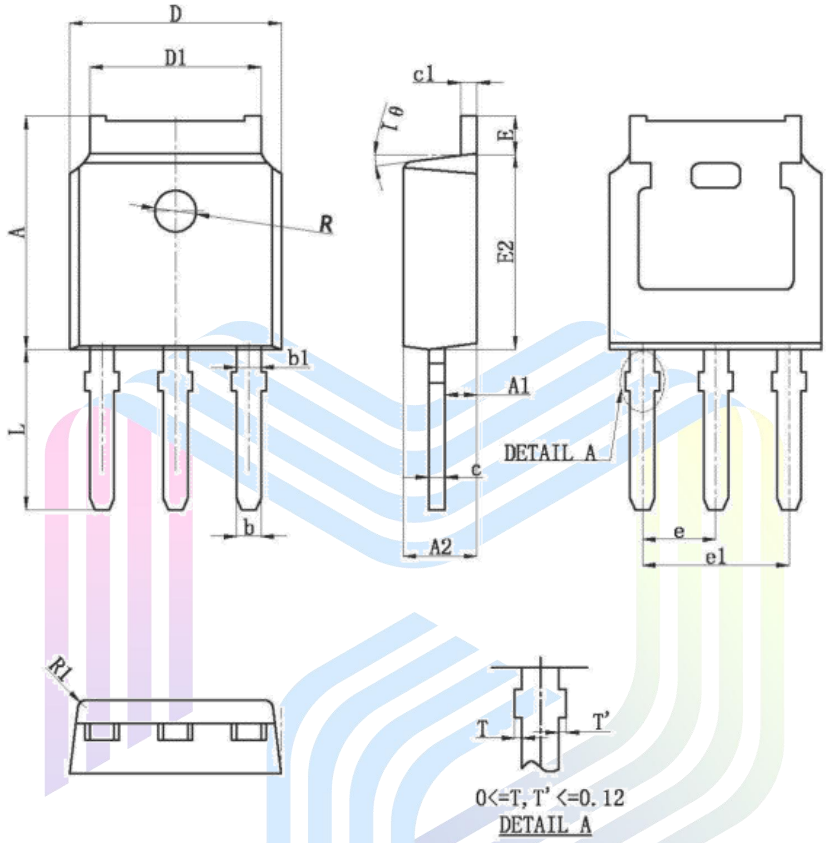


Figure 8: Threshold Voltage



Mechanical Dimensions:

TO-251-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	7.050	7.150	0.278	0.281
A1	0.960	1.060	0.038	0.42
A2	2.250	2.350	0.089	0.93
b	0.760REF		0.030REF	
b1	1.000REF		0.040REF	
c	0.508REF		0.02REF	
c1	0.508REF		0.02REF	
D	6.550	6.650	0.258	0.262
D1	5.220	5.420	0.206	0.213
E	0.950	1.050	0.037	0.041
E2	6.050	6.150	0.238	0.242
e	2.286BSC		0.09BSC	
e1	4.472REF		0.176REF	
L	4.800	5.200	0.189	0.205
θ1	7°REF		7°REF	
R	0.250REF		0.010REF	

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Via-Media Semiconductor Limited Company

http://www.vmdsemi.com

Main Sites:

- **Headquarters**

Hangzhou Via-Media Semiconductor Co., LTD.
1305-1306, Building 71, No. 90, Wensan Road, Xihu District, Hangzhou, Zhejiang Province, P.R. China
Tel: +86-0571-8515 0563

- **Chengdu Office**

Chengdu Winhi Semiconductor Co., LTD.
Floor 15, Building 5, No. 171, Hele 2nd Street, Chengdu, Sichuan Province, P.R. China
Tel: +86-028-8505 0771

- **Shanghai**

Shanghai R&D Center.
1506~1508, Xinyin Building, 888 Yishan Road, Shanghai, P.R of China
Tel: +86- 021-54201999

- **Shenzhen**

Shenzhen Sales office
Room 4A15, Block AB, Tianxiang Building, Chegongmiao , Futian District, Shenzhen, P.R of China
Tel: +86-0755- 82570682

- **Xi'an**

Xi'an R&D Center
1703B, Building A, Greenland Center, Jinye Road, High-Tech Zone, Xi'an, Shaanxi, P.R of China